

## 参数表

**2CLGA8KV-500mA** 高压高频二极管高可靠性台面结构及扩散工艺，环氧树脂真空灌注密闭封装。

**2CLGA8KV-500mA** High voltage rectifier diode adopts high reliable mesa structure and diffusion craftwork, epoxy resin molded in a compact structure.

### ▼ 产品特点 Feature

- ❖ 雪崩电压击穿保护特性 **Avalanche Characteristic**
- ❖ 优异的抗浪涌电流冲击特性 **Excellent surge current resistance**
- ❖ 高速开关响应特性 **High speed switch response characteristics**
- ❖ 采用新型环氧树脂真空封装技术，表面具有抗腐蚀性  
**Epoxy resin molded in vacuum, have anticorrosion in the surface**
- ❖ 工作结温 -50°C—+175°C **Tj:50°C—+175°C**
- ❖ 特殊耐高温性能芯片，可承受严酷恶劣的使用条件  
**Special high temperature resistant chip that can withstand harsh working**

conditions

### ▼ 产品 2D 图示

#### Graphical Representation

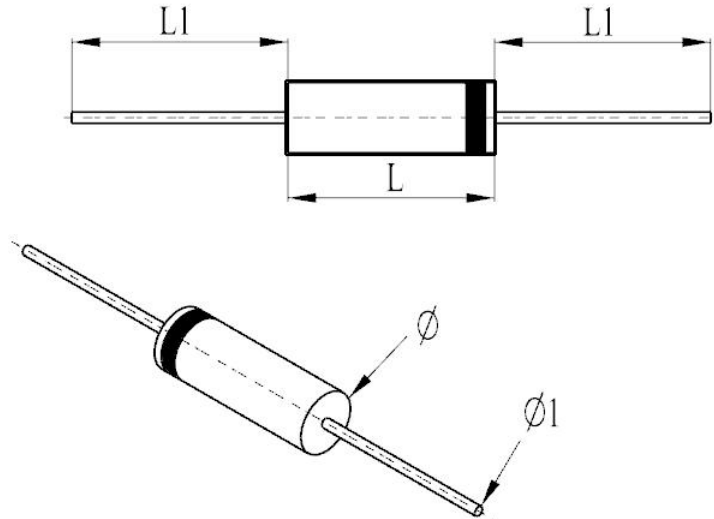


	参数名称 Item	符号 Symbol	单位 Unit	测试条件 Conditions	数值 Rating
Absolute Maximum Ratings 极限值 (绝对最大值)	反向重复峰值电压 Repetitive Peak Reverse Voltage	$V_{RRM}$	KV	Ta=25°C I <sub>R</sub> =2.0μA	8.0
	反向工作峰值电压) Peak Working Revere Voltage	$V_{RWM}$	KV	Ta=25°C I <sub>R</sub> =2.0μA	8.0
	正向平均电流 Average Forward Current	I <sub>F(AV)</sub>	A	正弦半波 50Hz, 电阻负载, T <sub>break</sub> =50°C ( 50Hz Half-sine Wave , Resistance load @T <sub>break</sub> =50°C )	0.5
	反向恢复时间 Reverse Recovery Time	t <sub>rr</sub>	nS		80
	正向(不重复)浪涌电流 Surge Forward Current	I <sub>FSM</sub>	A	正弦半波持续时间 0.01S 50Hz 0.01S @ Half-Sine wave 50Hz	30
	工作环境温度 Operating Ambient Temperature	T <sub>a</sub>	°C		-55 ~ +150
	存储温度 Storage Temperature	T <sub>stg</sub>	°C		-40 ~ +130
Electrical Characteristics 电特性	正向峰值电压 Forward Peak Voltage	V <sub>FM</sub>	V	@ Ta=25°C I <sub>f</sub> =500mA	12
	反向峰值电流 Peak Reverse Current	I <sub>RRM1</sub>	μA	@ Ta=25°C V <sub>RM</sub> =V <sub>RRM</sub>	0.5
		I <sub>RRM2</sub>	μA	@ Ta=100°C V <sub>RM</sub> =V <sub>RRM</sub>	20.0

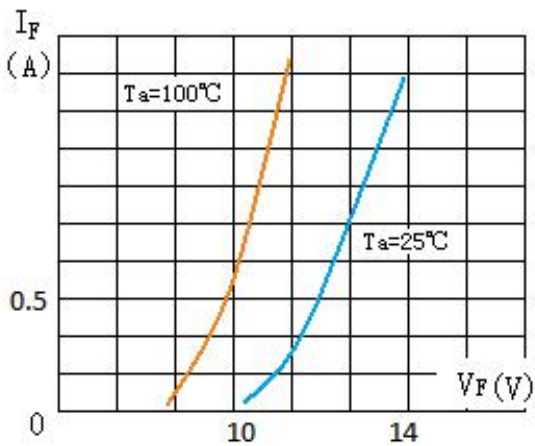
▼ 外形尺寸图示 Outline Drawings

(单位：毫米 mm)

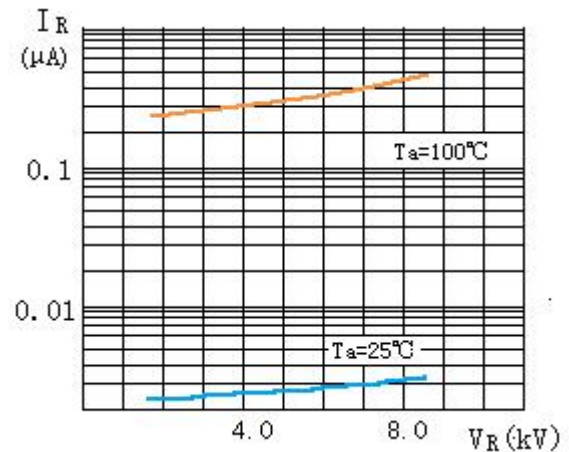
型号	直径 (Φ)	长 (L)	线径 (Φ1)	线长 (L1)
2CLGA8KV-500mA	7.5	22	1.2	>20
2CLG8KV-500mA	4.5	15	1.0	>20



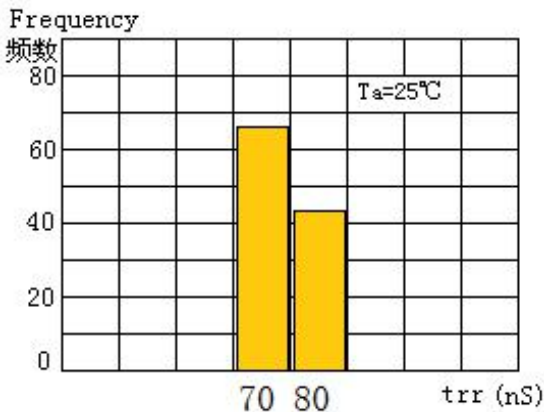
▼ 特性曲线图 Characteristic Curve



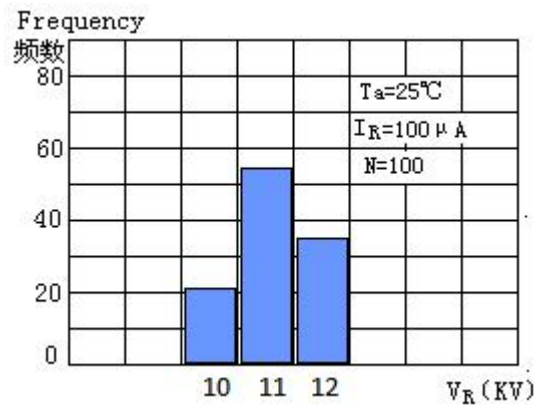
正向特性曲线 (2CLGA8KV-500mA)  
Forward Characteristics



反向特性曲线 (2CLGA8KV-500mA)  
Reverse Characteristics



反向恢复时间分布 (2CLGA8KV-500mA)  
Reverse Recovery Time



反向雪崩电压分布 (2CLGA8KV-500mA)  
Avalanche Breakdown Voltage Distribution